

TOSHIBA CMOS DIGITAL INTEGRATED CIRCUIT SILICON MONOLITHIC

TC74HC365AP, TC74HC365AF

TC74HC366AP, TC74HC366AF

HEX BUS BUFFER

TC74HC365AP/AF NON - INVERTED (3-STATE)
 TC74HC366AP/AF INVERTED (3-STATE)

The TC74HC365A and TC74HC366A are high speed CMOS 3 - STATE BUFFERS fabricated with silicon gate C²MOS technology.

They achieve the high speed operation similar to equivalent LSTTL while maintaining the CMOS low power dissipation.

The TC74HC366A is an inverting type, while the TC74HC365A is non - inverting.

All six buffers are controlled by the combination of two enable inputs ($\overline{G1}$ and $\overline{G2}$); the outputs of these buffers are enabled only when both $\overline{G1}$ and $\overline{G2}$ inputs held low, and at the other combinations, these outputs are disabled to the high impedance state.

All inputs are equipped with protection circuits against static discharge or transient excess voltage.

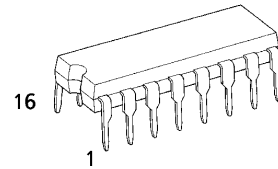
FEATURES:

- High Speed..... $t_{pd} = 9\text{ns}(\text{typ.})$ at $V_{CC} = 5\text{V}$
- Low Power Dissipation..... $I_{CC} = 4\mu\text{A}(\text{Max.})$ at $T_a = 25^\circ\text{C}$
- High Noise Immunity..... $V_{NIH} = V_{NIL} = 28\% V_{CC}(\text{Min.})$
- Output Drive Capability..... 15 LSTTL Loads
- Symmetrical Output Impedance... $|I_{OH}| = I_{OL} = 6\text{mA}(\text{Min.})$
- Balanced Propagation Delays..... $t_{PLH} \approx t_{PHL}$
- Wide Operating Voltage Range.... $V_{CC}(\text{opr.}) = 2\text{V} \sim 6\text{V}$
- Open Drain Structure
- Pin and Function Compatible with 74LS365/366

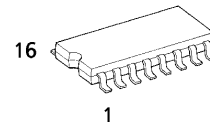
TRUTH TABLE

INPUTS			OUTPUTS	
$\overline{G1}$	$\overline{G2}$	A_n	$Y_n(365A)$	$\overline{Y}_n(366A)$
L	L	L	L	H
L	L	H	H	L
H	X	X	Z	Z
X	H	X	Z	Z

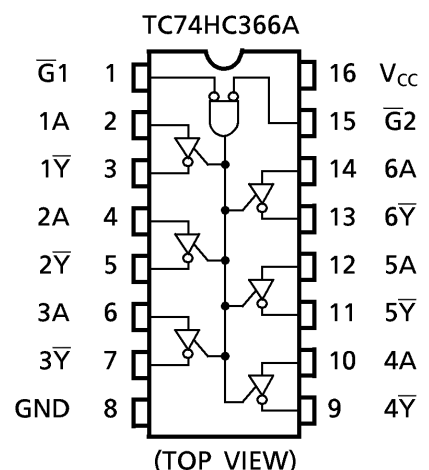
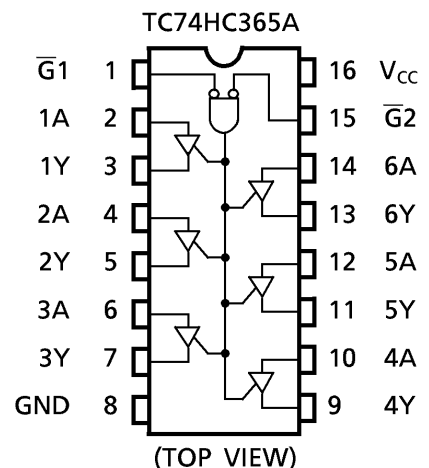
X : Don't Care, Z : High Impedance



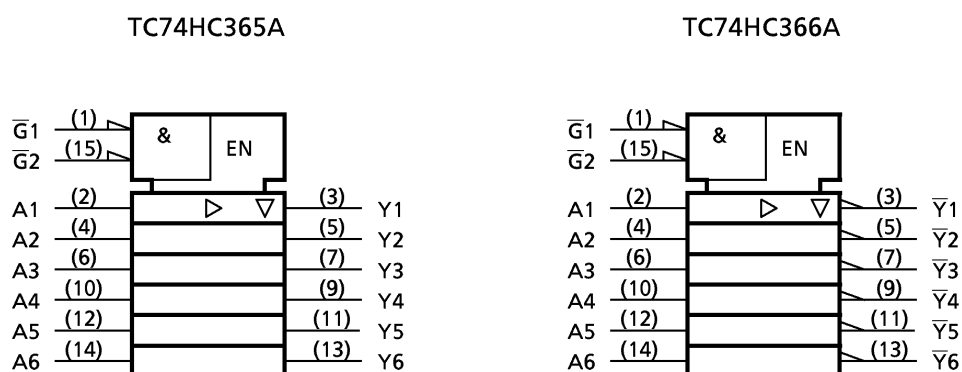
P (DIP16-P-300-2.54A)
 Weight : 1.00g (Typ.)



F (SOP16-P-300-1.27)
 Weight : 0.18g (Typ.)

PIN ASSIGNMENT

IEC LOGIC SYMBOL



ABSOLUTE MAXIMUM RATINGS

PARAMETER	SYMBOL	VALUE	UNIT
Supply Voltage Range	V_{CC}	$-0.5 \sim 7$	V
DC Input Voltage	V_{IN}	$-0.5 \sim V_{CC} + 0.5$	V
DC Output Voltage	V_{OUT}	$-0.5 \sim V_{CC} + 0.5$	V
Input Diode Current	I_{IK}	± 20	mA
Output Diode Current	I_{OK}	± 20	mA
DC Output Current	I_{OUT}	± 35	mA
DC V_{CC} /Ground Current	I_{CC}	± 75	mA
Power Dissipation	P_D	500 (DIP)* / 180 (SOP)	mW
Storage Temperature	T_{stg}	$-65 \sim 150$	°C

*500mW in the range of $T_a = -40^\circ\text{C} \sim 65^\circ\text{C}$. From $T_a = 65^\circ\text{C}$ to 85°C a derating factor of $-10\text{mW}/^\circ\text{C}$ shall be applied until 300mW.

RECOMMENDED OPERATING CONDITIONS

PARAMETER	SYMBOL	VALUE	UNIT
Supply Voltage	V_{CC}	$2 \sim 6$	V
Input Voltage	V_{IN}	$0 \sim V_{CC}$	V
Output Voltage	V_{OUT}	$0 \sim V_{CC}$	V
Operating Temperature	T_{opr}	$-40 \sim 85$	°C
Input Rise and Fall Time	t_r, t_f	$0 \sim 1000 (V_{CC} = 2.0\text{V})$ $0 \sim 500 (V_{CC} = 4.5\text{V})$ $0 \sim 400 (V_{CC} = 6.0\text{V})$	ns

DC ELECTRICAL CHARACTERISTICS

PARAMETER	SYMBOL	TEST CONDITION	V_{CC} (V)	$T_a = 25^\circ\text{C}$			$T_a = -40 \sim 85^\circ\text{C}$		UNIT
				MIN.	TYP.	MAX.	MIN.	MAX.	
High - Level Input Voltage	V_{IH}		2.0 4.5 6.0	1.50 3.15 4.20	— — —	— — —	1.50 3.15 4.20	— — —	V
Low - Level Input Voltage	V_{IL}		2.0 4.5 6.0	— — —	— — —	0.50 1.35 1.80	— — —	0.50 1.35 1.80	V
High - Level Output Voltage	V_{OH}	$V_{IN} = V_{IH} \text{ or } V_{IL}$ $I_{OH} = -20\mu\text{A}$	2.0 4.5 6.0	1.9 4.4 5.9	2.0 4.5 6.0	— — —	1.9 4.4 5.9	— — —	V
		$I_{OH} = -6 \text{ mA}$ $I_{OH} = -7.8 \text{ mA}$	4.5 6.0	4.18 5.68	4.31 5.80	— —	4.13 5.63	— —	
Low - Level Output Voltage	V_{OL}	$V_{IN} = V_{IH} \text{ or } V_{IL}$ $I_{OL} = 20\mu\text{A}$	2.0 4.5 6.0	— — —	0.0 0.0 0.0	0.1 0.1 0.1	— — —	0.1 0.1 0.1	V
		$I_{OL} = 6 \text{ mA}$ $I_{OL} = 7.8 \text{ mA}$	4.5 6.0	— —	0.17 0.18	0.26 0.26	— —	0.33 0.33	
3 - State Output Off - State Current	I_{OZ}	$V_{IN} = V_{IH} \text{ or } V_{IL}$ $V_{OUT} = V_{CC} \text{ or GND}$	6.0	—	—	± 0.5	—	± 5.0	μA
Input Leakage Current	I_{IN}	$V_{IN} = V_{CC} \text{ or GND}$	6.0	—	—	± 0.1	—	± 1.0	
Quiescent Supply Current	I_{CC}	$V_{IN} = V_{CC} \text{ or GND}$	6.0	—	—	4.0	—	40.0	

AC ELECTRICAL CHARACTERISTICS (Input $t_r = t_f = 6\text{ns}$)

PARAMETER	SYMBOL	TEST CONDITION			Ta = 25°C			Ta = -40~85°C		UNIT
			CL (pF)	V _{CC} (V)	MIN.	TYP.	MAX.	MIN.	MAX.	
Output Transition Time	t _{TLH} t _{THL}		50	2.0	—	20	60	—	75	ns
				4.5	—	6	12	—	15	
				6.0	—	5	10	—	13	
Propagation Delay Time	t _{pLH} t _{pHL}		50	2.0	—	38	90	—	115	
				4.5	—	12	18	—	23	
				6.0	—	10	15	—	20	
			150	2.0	—	51	130	—	165	
				4.5	—	17	26	—	33	
				6.0	—	14	22	—	28	
Output Enable Time	t _{pZL} t _{pZH}	R _L = 1kΩ	50	2.0	—	56	130	—	165	
				4.5	—	17	26	—	33	
				6.0	—	13	22	—	28	
			150	2.0	—	69	170	—	215	
				4.5	—	22	34	—	44	
				6.0	—	17	29	—	37	
Output Disable Time	t _{pLZ} t _{pHZ}	R _L = 1kΩ	50	2.0	—	42	130	—	165	
				4.5	—	18	26	—	33	
				6.0	—	15	22	—	28	
Input Capacitance	C _{IN}				—	5	10	—	10	pF
Output Capacitance	C _{OUT}				—	10	—	—	—	
Power Dissipation Capacitance	C _{PD} (1)				—	25	—	—	—	

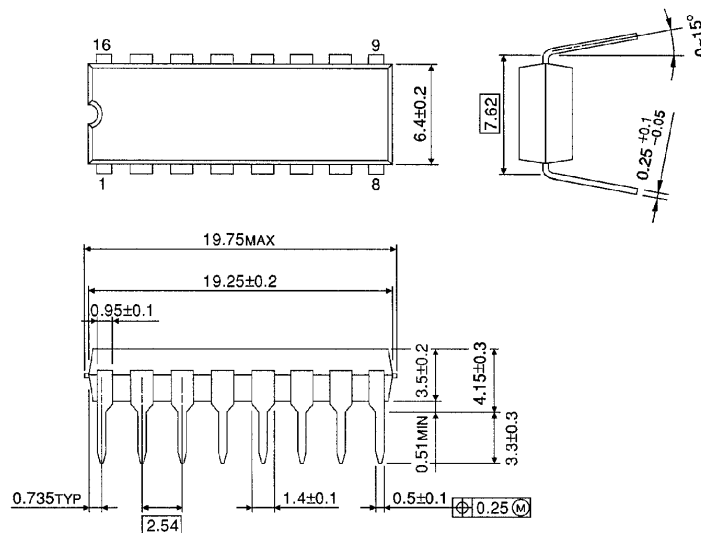
Note (1) C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load.

Average operating current can be obtained by the equation :

$$I_{CC}(\text{opr}) = C_{PD} \cdot V_{CC} \cdot f_{IN} + I_{CC}/6 \text{ (per Gate)}$$

DIP 16PIN PACKAGE DIMENSIONS (DIP16-P-300-2.54A)

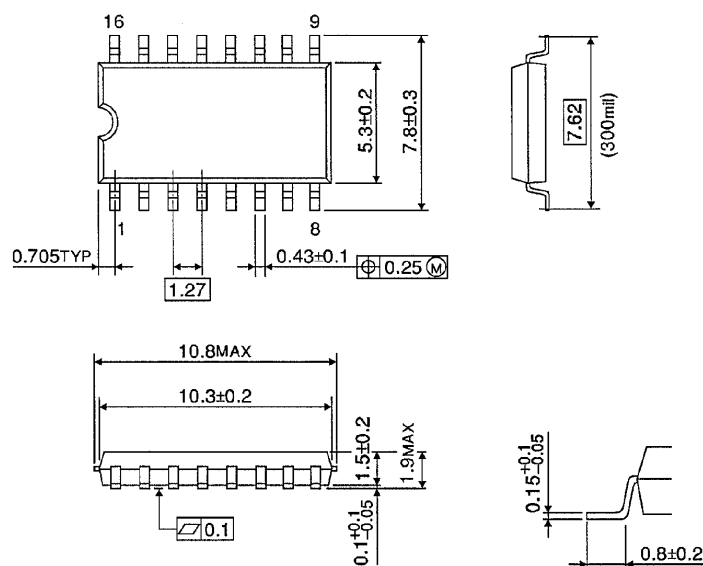
Unit in mm



Weight : 1.00g (Typ.)

SOP 16PIN (200mil BODY) PACKAGE DIMENSIONS (SOP16-P-300-1.27)

Unit in mm



Weight : 0.18g (Typ.)

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000707EBA

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